

# **DATA SHEET**

# **Darlington transistors**

Order code	Manufacturer code	Description		
81-0106	BD679	BD679 NPN POWER DARLINGTON		

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The enclosed information is believed to be correct, Information may change 'without notice' due to	Revision A
product improvement. Users should ensure that the product is suitable for their use. E. & O. E.	04/07/2003

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## BD677/A/679/A681 BD678/A/680/A/682

# COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

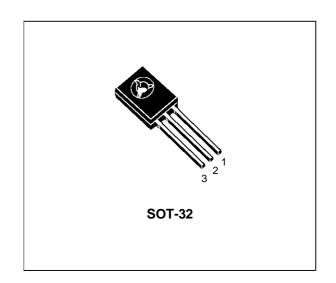
#### ■ SGS-THOMSON PREFERRED SALESTYPES

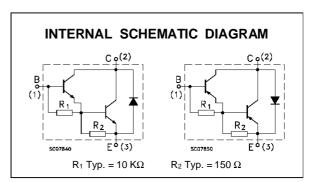
#### **DESCRIPTION**

The BD677, BD677A, BD679, BD679A and BD681 are silicon epitaxial-base NPN power transistors in monolithic Darlington configuration mounted in Jedec SOT-32 plastic package.

They are intended for use in medium power linar and switching applications

The complementary PNP types are BD678, BD678A, BD680, BD680A and BD682 respectively.





#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter			Unit		
		NPN	BD677/A	BD679/A	BD681	
		PNP	BD678/A	BD680/A	BD682	
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)		60	80	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)		60	80	100	V
$V_{EBO}$	Emitter-Base Voltage (I <sub>C</sub> = 0)		5			V
Ic	Collector Current		4			Α
Ісм	Collector Peak Current		6			Α
$I_{B}$	Base Current			0.1		А
Ptot	Total Dissipation at T <sub>c</sub> ≤ 25 °C			40		W
T <sub>stg</sub>	Storage Temperature		-65 to 150			°C
Tj	Max. Operating Junction Temperature		150			°C

For PNP types voltage and current values are negative.

October 1995 1/4

### BD677/677A/678/678A/679/679A/680/680A/681/682

#### THERMAL DATA

Ī	R <sub>thj-case</sub>	Thermal Resistance	Junction-case	Max	3.12	°C/W
	$R_{thj-amb}$	Thermal Resistance	Junction-ambient	Max	100	°C/W

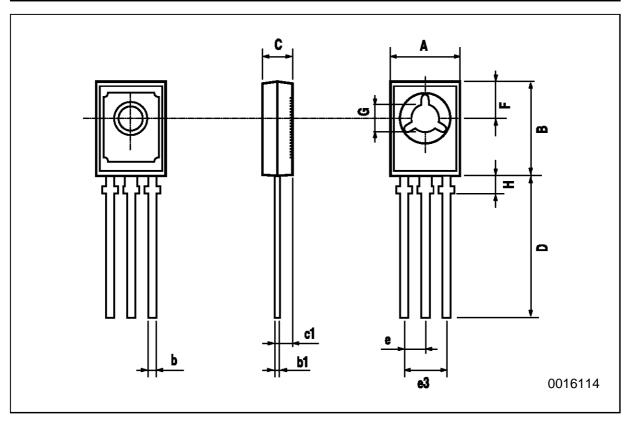
## **ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	$V_{CE}$ = rated $V_{CBO}$ $V_{CE}$ = rated $V_{CBO}$ $T_{C}$ = 100 $^{\circ}$ C			0.2 2	mA mA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = half rated V <sub>CEO</sub>			0.5	mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			2	mA
VCEO(sus)*	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50 mA for BD677/677A/678/678A for BD679/679A/680/680A for BD681/682	60 80 100			V V V
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	for BD677/678/679/680/681/682 $I_C = 1.5 \text{ A}$ $I_B = 30 \text{ mA}$ for BD677A/678A/679A/680A $I_C = 2 \text{ A}$ $I_B = 40 \text{ mA}$			2.5 2.8	V
V <sub>BE</sub> *	Base-Emitter Voltage	for <b>BD677/678/679/680/681/682</b> I <sub>C</sub> = 1.5 A V <sub>CE</sub> = 3 V for <b>BD677A/678A/679A/680A</b> I <sub>C</sub> = 2 A V <sub>CE</sub> = 3 V			2.5 2.5	V V
h <sub>FE</sub> *	DC Current Gain	for <b>BD677/678/679/680/681/682</b> I <sub>C</sub> = 1.5 A V <sub>CE</sub> = 3 V for <b>BD677A/678A/679A/680A</b> I <sub>C</sub> = 2 A V <sub>CE</sub> = 3 V	750 750			
h <sub>fe</sub>	Small Signal Current Gain	$I_C = 1.5 \text{ A}$ $V_{CE} = 3 \text{ V}$ $f = 1 \text{MHz}$	1			

<sup>\*</sup> Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

## **SOT-32 MECHANICAL DATA**

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	7.4		7.8	0.291		0.307	
В	10.5		10.8	0.413		0.445	
b	0.7		0.9	0.028		0.035	
b1	0.49		0.75	0.019		0.030	
С	2.4		2.7	0.04		0.106	
c1		1.2			0.047		
D		15.7			0.618		
е		2.2			0.087		
e3		4.4			0.173		
F		3.8			0.150		
G	3		3.2	0.118		0.126	
Н			2.54			0.100	



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